TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSVI)

# **TPC8120**

# Lithium Ion Battery Applications Power Management Switch Applications

Unit: mm

- Small footprint due to small and thin package
- Low drain-source ON-resistance:  $RDS(ON) = 2.6 \text{ m}\Omega \text{ (typ.)}$
- High forward transfer admittance:  $|Y_{fs}| = 80 \text{ S}$  (typ.)
- Low leakage current:  $IDSS = -10 \mu A (max) (VDS = -30 V)$
- Enhancement mode:  $V_{th} = -0.8 \text{ to } -2.0 \text{ V } (V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA})$

#### **Absolute Maximum Ratings (Ta = 25°C)**

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	-30	V	
Drain-gate voltage (Ro	$_{\rm SS} = 20 \; \rm k\Omega)$	$V_{DGR}$	-30	V	
Gate-source voltage		$V_{GSS}$	-25/+20	V	
Drain current	DC (Note 1)	ΙD	-18	Α	
	Pulse (Note 1)	$I_{DP}$	-72	A	
Drain power dissipatio	n (t = 10 s) (Note 2a)	$P_{D}$	1.9	W	
Drain power dissipatio	n (t = 10 s) (Note 2b)	P <sub>D</sub>	1.0	W	
Single pulse avalanche	e energy (Note 3)	E <sub>AS</sub>	211	mJ	
Avalanche current		I <sub>AR</sub>	-18	Α	
Repetitive avalanche e	energy lote 2a) (Note 4)	E <sub>AR</sub>	0.03	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature ra	ange	T <sub>stg</sub>	-55 to 150	°C	

Note 1, Note 2, Note 3 and Note 4: See the next page.

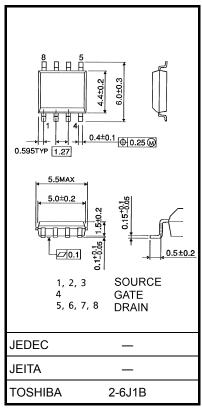
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating

temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating

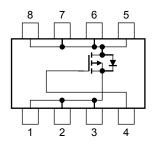
Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.080 g (typ.)

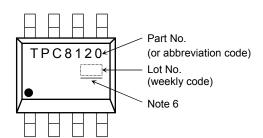
### **Circuit Configuration**



#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	125	°C/W

#### Marking (Note 5)



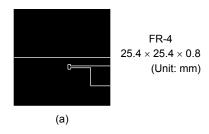
Note 6: A line under a Lot No. identifies the indication of product Labels [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

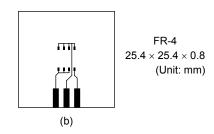
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)





Note 3:  $V_{DD} = -24~V$ ,  $T_{ch} = 25^{\circ}C$  (initial),  $L = 500~\mu H$ ,  $R_G = 25~\Omega$ ,  $I_{AR} = -18~A$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on lower left of the marking indicates Pin 1.

Weekly code: (Three digits)
 Week of manufacture
 (01 for the first week of a year: sequential number up to 52 or 53)
 Year of manufacture
 (The last digit of a year)

2

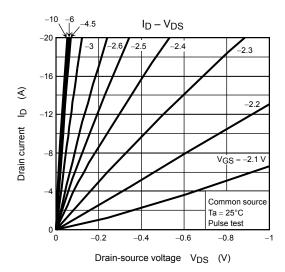
# Electrical Characteristics (Ta = 25°C)

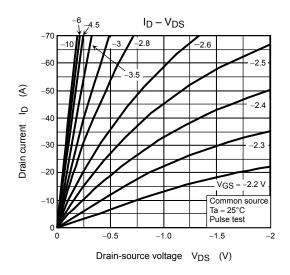
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curre	nt	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cut-OFF curre	ent	I <sub>DSS</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	_	_	-10	μА
Drain-source break	down voltage	V <sub>(BR)DSS</sub>	$I_D = -10$ mA, $V_{GS} = 0$ V	-30	_		V
Dialii-30dice bleak	down voltage	V <sub>(BR)DSX</sub>	$I_D = -10 \text{ mA}, V_{GS} = 10V \text{ (Note 7)}$	-21	_		٧
Gate threshold volt	age	V <sub>th</sub>	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	-0.8	_	-2.0	>
Drain-source ON-resistance		D	$V_{GS} = -4.5 \text{ V}, I_D = -9 \text{ A}$		3.3	4.2	mΩ
Dialii-source ON-16	esisianice	R <sub>DS</sub> (ON)	$V_{GS} = -10 \text{ V}, I_D = -9 \text{ A}$		2.6	3.2	1112.2
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = -10 \text{ V}, I_D = -9 \text{ A}$	40	80		S
Input capacitance		C <sub>iss</sub>			7420		pF
Reverse transfer capacitance		C <sub>rss</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	1180	_	
Output capacitance		Coss		_	1440	_	
- Catput supusitans	Rise time	t <sub>r</sub>	Vcs		10		
Switching time	Turn-ON time	t <sub>on</sub>	VGS _10 V	S = 0 V	_		
Switching time	Fall time	t <sub>f</sub>	Ľ.	_	275	_	ns
	Turn-OFF time	t <sub>off</sub>	$V_{DD} \approx -15 \text{ V}$ Duty ≤ 1%, $t_W = 10 \text{ μs}$		790		
Total gate charge (gate-source plus g	ate-drain)	Qg	V <sub>DD</sub> ≈ -24 V, V <sub>GS</sub> = -10 V,	_ 180		_	
Gate-source charge 1		Q <sub>gs1</sub>	$I_D = -18 \text{ A}$	_	20	_	nC
Gate-drain ("miller") charge		Q <sub>gd</sub>		_	40	_	

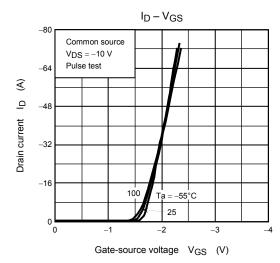
## **Source-Drain Ratings and Characteristics (Ta = 25°C)**

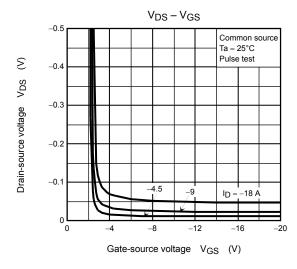
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	-72	Α
Forward voltage (diode)		V <sub>DSF</sub>	$I_{DR} = -18 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	1.2	V	

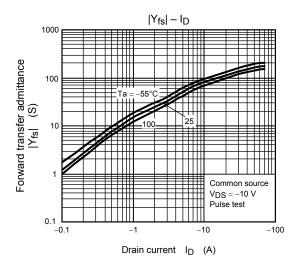
Note 7: V<sub>DSX</sub> mode (the application of a plus voltage between gate and source) may cause decrease in maximum rating of drain-source voltage.

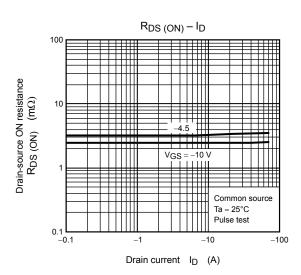


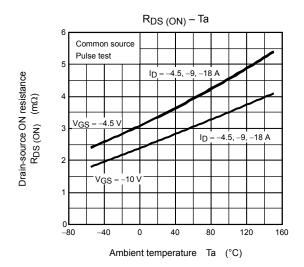


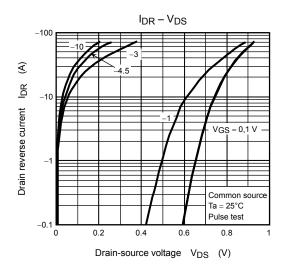


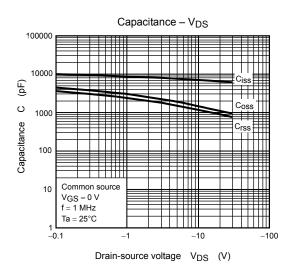


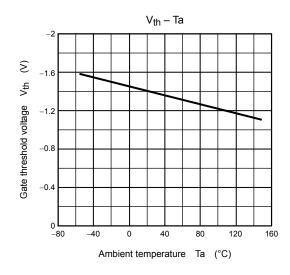


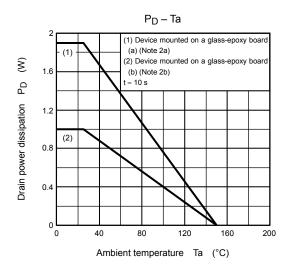


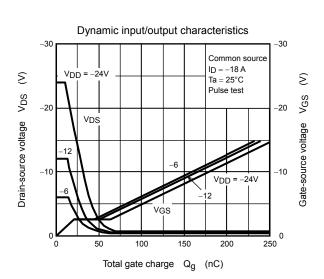


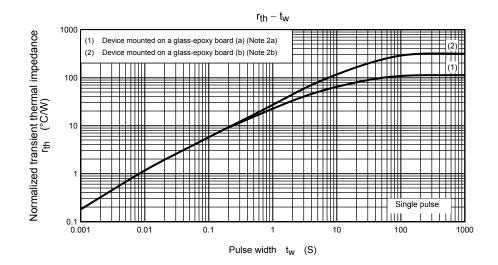


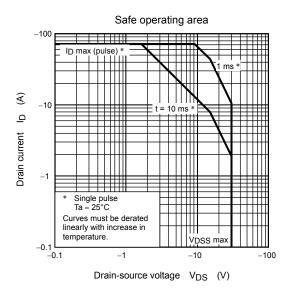












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